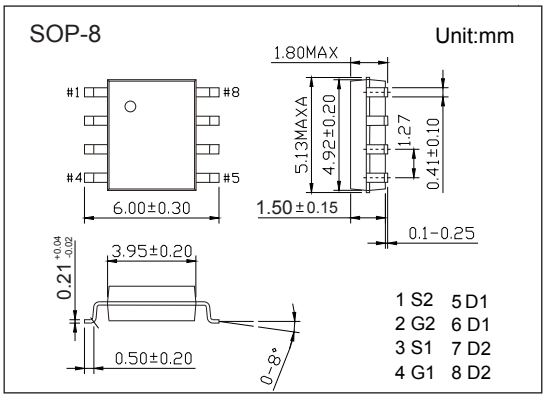
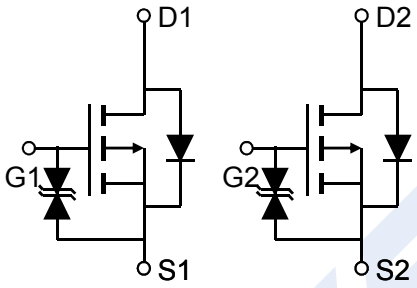
Dual P-Channel MOSFET
AO4817-HF (KO4817-HF)



■ Features

- V_{DS} (V) = -30V
- I_D = -8 A (V_{GS} = -20V)
- $R_{DS(ON)}$ < 18mΩ (V_{GS} = -20V)
- $R_{DS(ON)}$ < 21mΩ (V_{GS} = -10V)
- ESD Rating: 1.5KV HBM
- Pb−Free Package May be Available. The G−Suffix Denotes a Pb−Free Lead Finish



■ Absolute Maximum Ratings Ta = 25℃

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±25	
Continuous Drain Current	T_A=25℃	I_D	-8	A
	T_A=70℃		-6.9	
Pulsed Drain Current		I_{DM}	-40	
Power Dissipation	T_A=25℃	P_D	2	W
	T_A=70℃		1.44	
Thermal Resistance.Junction- to-Ambient	t ≤ 10s	R_{thJA}	62.5	℃/W
	Steady-State		110	
Thermal Resistance.Junction- to-Lead		R_{thJL}	40	
Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{stg}	-55 to 150	

Dual P-Channel MOSFET
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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=-250μA, V_{GS}=0V	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V, V_{GS}=0V			-1	uA
		V_{DS}=-24V, V_{GS}=0V, T_J=55℃			-5	
Gate-Body Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±25V			±1	uA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} , I_D=-250uA	-1		-3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-20V, I_D=-8A			18	mΩ
		V_{GS}=-20V, I_D=-8A T_J=125℃			25	
		V_{GS}=-10V, I_D=-8A			21	
		V_{GS}=-4.5V, I_D=-4A		44		
On State Drain Current	$I_{D(ON)}$	V_{GS}=-10V, V_{DS}=-5V	-40			A
Forward Transconductance	g_{FS}	V_{DS}=-5V, I_D=-8A		15		S
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-15V, f=1MHz		1760	2200	pF
Output Capacitance	C_{oss}			360		
Reverse Transfer Capacitance	C_{rss}			255		
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz		6.4	8	Ω
Total Gate Charge	Q_g	V_{GS}=-10V, V_{DS}=-15V, I_D=-8A		30	38	nC
Gate Source Charge	Q_{gs}			7		
Gate Drain Charge	Q_{gd}			8		
Turn-On DelayTime	$t_{d(on)}$	V_{GS}=-10V, V_{DS}=-15V, R_L=1.8Ω, R_{GEN}=3Ω		12.5		ns
Turn-On Rise Time	t_r			10.5		
Turn-Off DelayTime	$t_{d(off)}$			40		
Turn-Off Fall Time	t_f			23		
Body Diode Reverse Recovery Time	t_{rr}	I_F= -8A, dI/dt= 100A/us		24	30	
Body Diode Reverse Recovery Charge	Q_{rr}			16		nC
Maximum Body-Diode Continuous Current	I_S				-2.6	A
Diode Forward Voltage	V_{SD}	I_S=-1A,V_{GS}=0V			-1	V

Note.The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

■ Marking

Marking	4817 KA**** F

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■ Typical Characterisitics

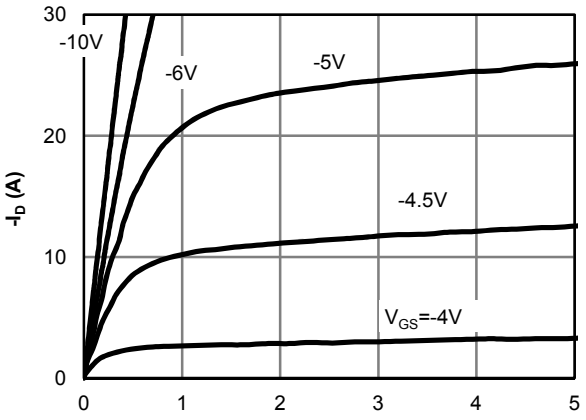

Fig 1: On-Region Characteristics

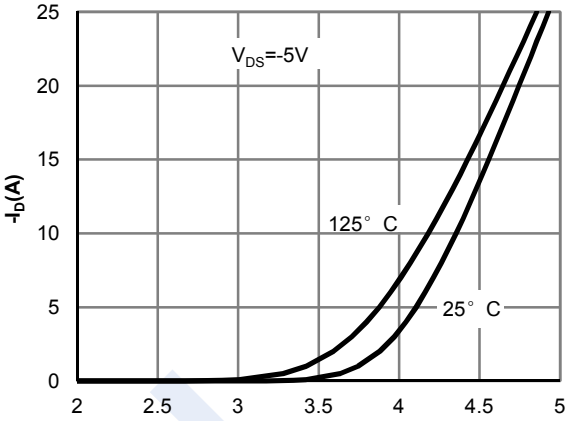

Figure 2: Transfer Characteristics

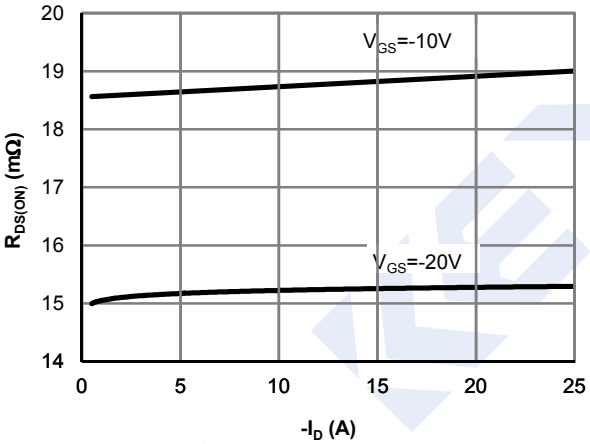

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

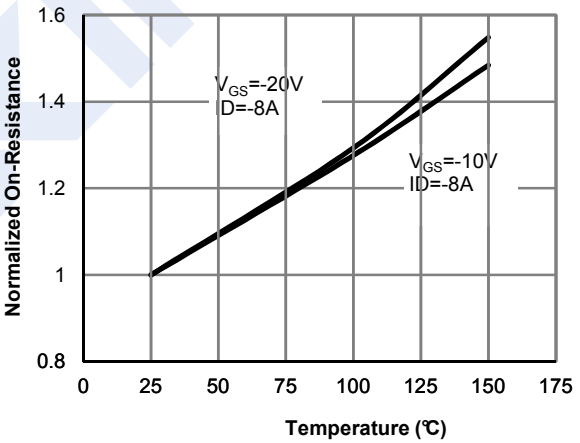

Figure 4: On-Resistance vs. Junction Temperature

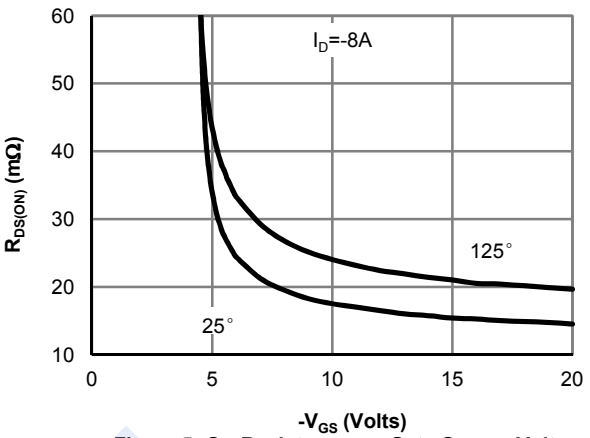

Figure 5: On-Resistance vs. Gate-Source Voltage

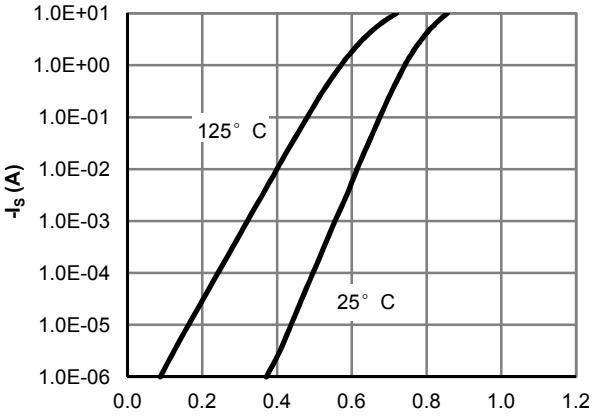

Figure 6: Body-Diode Characteristics

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■ Typical Characterisitics

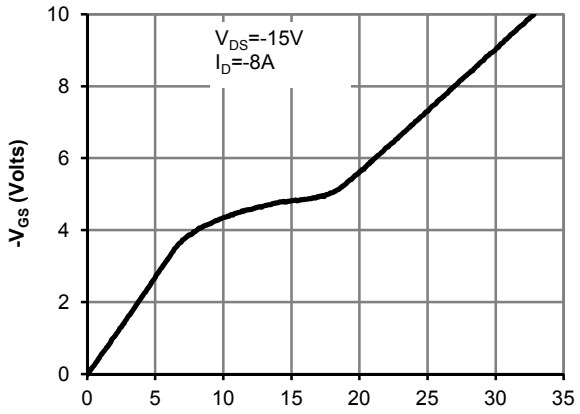

Figure 7: Gate-Charge Characteristics

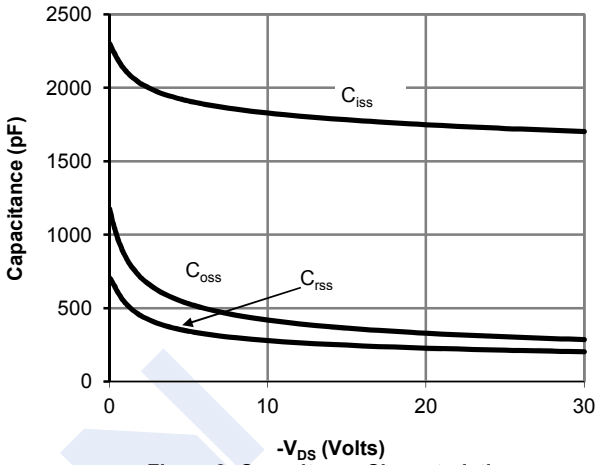

Figure 8: Capacitance Characteristics

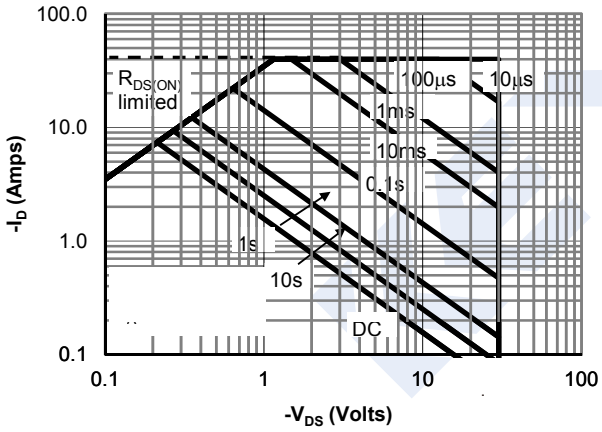

Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

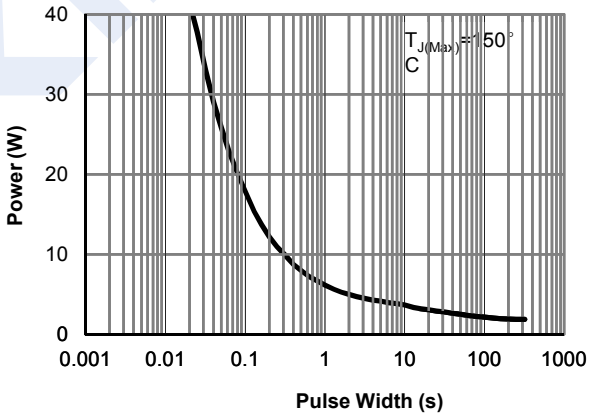

Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

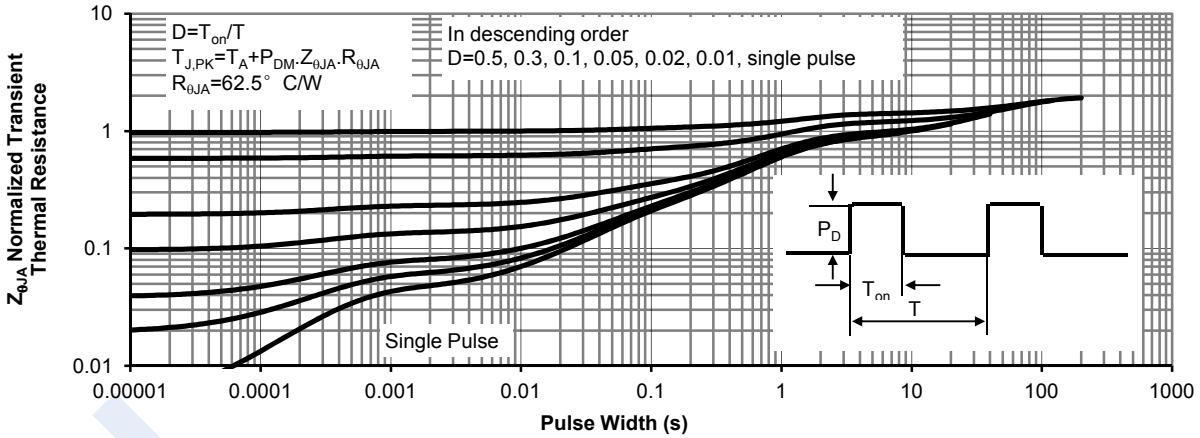

Figure 11: Normalized Maximum Transient Thermal Impedance